



INTEL® SOLID-STATE DRIVES: COMPARE PRODUCT FEATURES

FEATURES	INTEL® SSD DC S3700 SERIES	INTEL® SSD DC S3600 SERIES
Common Usage Models	Write-intensive workloads	Read-intensive workloads
High-Performing		
Form Factor/Capacity (GB)	2.5"and HHHL AIC: 400GB, 800GB, 1.6TB and 2.0TB	2.5"and HHHL AIC: 400GB, 800GB, 1.2TB, 1.6TB and 2.0TB
Interface	Non-Volatile Memory express (NVMe*) PCIe* 3.0x4	
Sequential Performance R/W (MB/sec)	Up to 2,800/2,000	2,600/1,700
Performance: 4K Random R/W (IOPS)	Up to 265,000	Up to 170,000
Performance: 8K Random R/W (IOPS)	295,000/90,000	275,000/35,000
Average Latency (µS)	20(µs)/ 20(µs)	
NAND Litho	Intel ® NAND Flash Memory Multi-Level Cell (MLC) 20nm	
Endurance	.3 drive writes per day	10 drive writes per day
Ease of Use		
Quality and Reliability	10 drive writes/day ¹	3 drive writes/day
Warranty	5 year	
Enhanced Security		
Security and Encryption	256-bit AES	
Total 4KB Random Writes	Up to 14.6PB	Up to 450TB (800GB)
Energy Efficiency		
Limit Inrush Current (Soft Start Circuit + Staggered Spin Up), Power-Safe Write Caching and Temperature Sensor		
Power (active/standby) (W)	Up to 5.0/0.95	6.0/0.65

1. Based on the Intel® Solid-State Drive DC S3700 Series Product Specification.

© 2014, Intel Corporation. All rights reserved. Intel and the Intel logo are trademarks of Intel Corporation in the U.S. and/or other countries.

*Other names and brands may be claimed as the property of others. 1114/SLH/CMD/PDF 331609-001